

54AC11030, 74AC11030 8-INPUT POSITIVE-NAND GATES

SCAS001A – JUNE 1987 – REVISED APRIL 1993

- Flow-Through Architecture Optimizes PCB Layout
- Center-Pin V_{CC} and GND Configurations Minimize High-Speed Switching Noise
- EPIC™ (Enhanced-Performance Implanted CMOS) 1- μ m Process
- 500-mA Typical Latch-Up Immunity at 125°C
- Package Options Include Plastic Small-Outline Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs

description

These devices contain a single 8-input NAND gate and perform the following Boolean functions in positive logic:

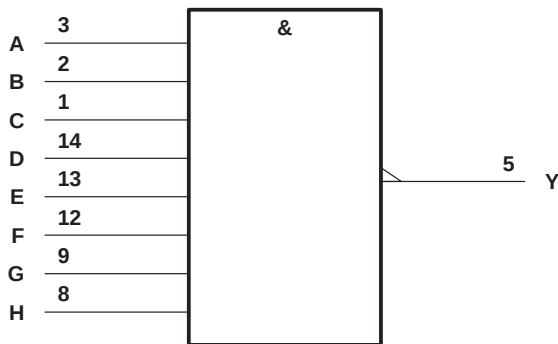
$$Y = \overline{A \cdot B \cdot C \cdot D \cdot E \cdot F \cdot G \cdot H} \text{ or } Y = \overline{A} + \overline{B} + \overline{C} + \overline{D} + \overline{E} + \overline{F} + \overline{G} + \overline{H}$$

The 54AC11030 is characterized for operation over the full military temperature range of –55°C to 125°C. The 74AC11030 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

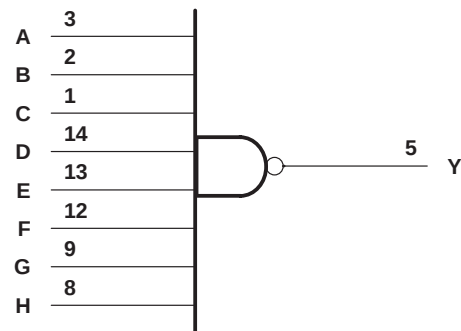
INPUTS A THRU H	OUTPUT Y
All inputs H	L
One or more inputs L	H

logic symbol†

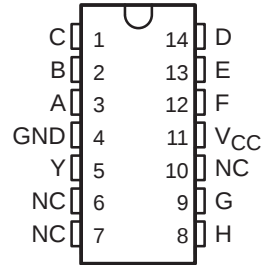


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, J, and N packages.

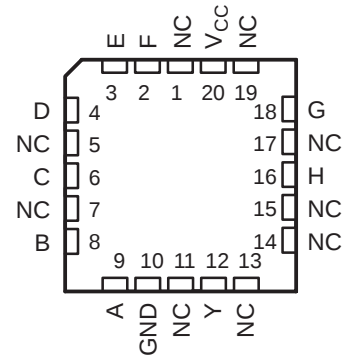
logic diagram (positive logic)



54AC11030 . . . J PACKAGE
74AC11030 . . . D OR N PACKAGE
(TOP VIEW)



54AC11030 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

EPIC is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

TEXAS
INSTRUMENTS

POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1993, Texas Instruments Incorporated

54AC11030, 74AC11030

8-INPUT POSITIVE-NAND GATES

SCAS001A – JUNE 1987 – REVISED APRIL 1993

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V_{CC}	–0.5 V to 6 V
Input voltage range, V_I (see Note 1)	–0.5 V to $V_{CC} + 0.5$ V
Output voltage range, V_O (see Note 1)	–0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)	±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Storage temperature range	–65°C to 150°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

recommended operating conditions

			54AC11030			74AC11030			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V _{CC}	Supply voltage		3	5	5.5	3	5	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 3 V	2.1			2.1			V
		V _{CC} = 4.5 V	3.15			3.15			
		V _{CC} = 5.5 V	3.85			3.85			
V _{IL}	Low-level input voltage	V _{CC} = 3 V	0.9			0.9			V
		V _{CC} = 4.5 V	1.35			1.35			
		V _{CC} = 5.5 V	1.65			1.65			
V _I	Input voltage		0	V _{CC}		0	V _{CC}		V
V _O	Output voltage		0	V _{CC}		0	V _{CC}		V
I _{OH}	High-level output current	V _{CC} = 3 V	−4			−4			mA
		V _{CC} = 4.5 V	−24			−24			
		V _{CC} = 5.5 V	−24			−24			
I _{OL}	Low-level output current	V _{CC} = 3 V	12			12			mA
		V _{CC} = 4.5 V	24			24			
		V _{CC} = 5.5 V	24			24			
Δt/Δv	Input transition rise or fall rate		0	10		0	10		ns/V
T _A	Operating free-air temperature		−55	125		−40	85		°C

54AC11030, 74AC11030 8-INPUT POSITIVE-NAND GATES

SCAS001A – JUNE 1987 – REVISED APRIL 1993

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			54AC11030		74AC11030		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	I _{OH} = – 50 µA	3 V	2.9			2.9		2.9		V
		4.5 V	4.4			4.4		4.4		
		5.5 V	5.4			5.4		5.4		
	I _{OH} = – 4 mA	3 V	2.58			2.4		2.48		
		4.5 V	3.94			3.7		3.8		
		5.5 V	4.94			4.7		4.8		
	I _{OH} = – 50 mA [†]	5.5 V				3.85				
	I _{OH} = – 75 mA [†]	5.5 V						3.85		
V _{OL}	I _{OL} = 50 µA	3 V			0.1		0.1		0.1	V
		4.5 V			0.1		0.1		0.1	
		5.5 V			0.1		0.1		0.1	
	I _{OL} = 12 mA	3 V			0.36		0.5		0.44	
		4.5 V			0.36		0.5		0.44	
		5.5 V			0.36		0.5		0.44	
	I _{OL} = 50 mA [†]	5.5 V				1.65				
	I _{OL} = 75 mA [†]	5.5 V						1.65		
I _I	V _I = V _{CC} or GND	5.5 V			±0.1		±1		±1	µA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V			4		80		40	µA
C _i	V _I = V _{CC} or GND	5 V		3.5						pF

[†] Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.

switching characteristics over recommended operating free-air temperature range,
V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T _A = 25°C			54AC11030		74AC11030		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	Any	Y	1.5	6.9	9.1	1.5	10.6	1.5	9.9	ns
t _{PHL}			1.5	6.4	8.8	1.5	10.6	1.5	9.8	

switching characteristics over recommended operating free-air temperature range,
V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T _A = 25°C			54AC11030		74AC11030		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	Any	Y	1.5	4.8	6.7	1.5	7.7	1.5	7.2	ns
t _{PHL}			1.5	4.8	6.7	1.5	8	1.5	7.4	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

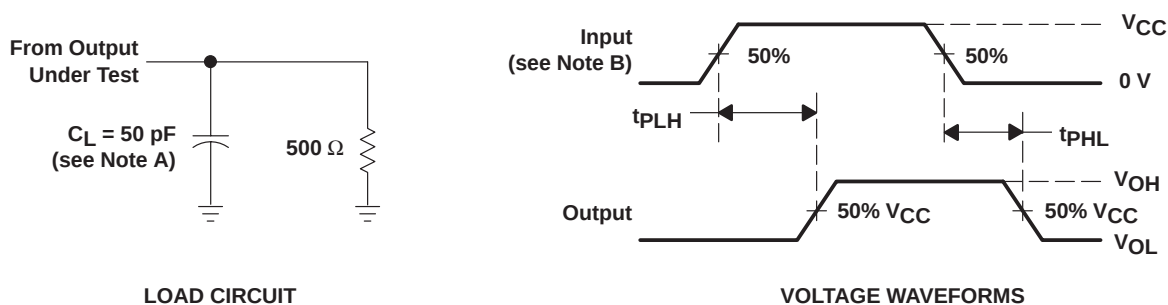
PARAMETER		TEST CONDITIONS		TYP	UNIT
C _{pd}	Power dissipation capacitance per gate	C _L = 50 pF, f = 1 MHz		42	pF

54AC11030, 74AC11030

8-INPUT POSITIVE-NAND GATES

SCAS001A – JUNE 1987 – REVISED APRIL 1993

PARAMETER MEASUREMENT INFORMATION



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r = 3 \text{ ns}$, $t_f = 3 \text{ ns}$.
 - C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.